

ADVISORY ON THE USE OF THIS DOCUMENT

The information contained in this document has been developed solely for the purpose of providing general guidance to employees of the Goddard Space Flight Center (GSFC). This document may be distributed outside GSFC only as a courtesy to other government agencies and contractors. Any distribution of this document, or application or use of the information contained herein, is expressly conditioned upon, and is subject to, the following understandings and limitations:

- (a) The information was developed for general guidance only and is subject to change at any time;
- (b) The information was developed under unique GSFC laboratory conditions which may differ substantially from outside conditions;
- (c) GSFC does not warrant the accuracy of the information when applied or used under other than unique GSFC laboratory conditions;
- (d) The information should not be construed as a representation of product performance by either GSFC or the manufacturer;
- (e) Neither the United States government nor any person acting on behalf of the United States government assumes any liability resulting from the application or use of the information.

UNISYS

102)

Interoffice Memorandum

PPM-91-754

Date

December 27, 1991

Location

Lanham

Telephone

731-8954

Location

Lanham

cc:

B. Fafaul/311
A. Sharma/311
D. Krus
J. Stubblefield
A. Moor
Library/311

To
T. Miccolis
Department
Code 300.1
From
K. Sahu KS
Department
7809
Subject
Radiation Report on SMEX
Common Buy Part No. 54AC521DMQB
Control No. 1661

A radiation evaluation was performed on the 54AC521 to determine the total dose tolerance of these parts. A brief summary of the test results is provided below. For detailed information, refer to Tables I through IV and Figure 1.

The total dose testing was performed using a cobalt-60 gamma ray source. During the radiation testing, eight parts were irradiated under bias (see Figure 1 for bias configuration), and two parts were used as control samples. The total dose radiation steps were 10, 20, 30, 50, 75 and 100 krads*. After 100 krads, parts were annealed at +25°C for 24 and 168 hours, and then irradiation was continued to 200 and 300 krads (cumulative). The parts were finally annealed at +100°C for 168 hours. The dose rate was between 0.5 and 5.2 krads/hour, depending on the total dose level (see Table II for radiation schedule). After each radiation exposure and annealing treatment, parts were electrically tested at +25°C according to the test conditions and the specification limits listed in Table III. These tests included a two functional tests (at 1 MHz) after each radiation and annealing step.

All eight parts passed both functional tests and all parametric tests, except ICCH and ICCL, throughout the radiation testing to 300 krads, and subsequent high temperature annealing for 168 hours. After the first radiation exposure to 10 krads, six of eight parts exceeded the maximum specification limit of 8uA for ICCH and five parts exceeded the same limit for ICCL. Maximum readings for these parameters were 280uA and 105uA, respectively. At 20 krads, all parts exceeded the specification limit for ICCH and ICCL. Readings for these parameters continued to increase with total doses to 100 krads. A slight decrease in ICCH/L was observed after 24 and 168 hours of annealing at 25°C, but average readings were still approximately 10mA. At 200 and 300 krads, average ICCH/L values increased to 20mA and 40mA, respectively.

On annealing the parts for 168 hours at 100°C, the parts showed significant recovery as the average ICCH/L readings dropped to approximately 4mA. Table IV provides the mean and standard deviation values for each parameter after different radiation exposures and annealing treatments. It also provides a summary of the functional test results at these steps in the testing.

Any further details about this evaluation can be obtained upon request. If you have any questions, please call me at (301)731-8954.

*In this report, the term "rads" is used as an abbreviation for rads (Si).

TABLE I. Part Information

Generic Part Number:	54AC521
SMEC Common Buy Part Number:	54AC521DMQB (HA124210)
SMEC Common Buy Control Number:	1661
Charge Number:	C90366
Manufacturer:	National Semiconductor Corp.
Quantity Procured:	118
Lot Date Code:	9038A
Quantity Tested:	10
Serial Numbers of Radiation Samples:	162, 163, 164, 165, 166, 167, 168, 169
Serial Numbers of Control Samples:	160, 161
Part Function:	8-Bit Identity Comparator
Part Technology:	CMOS
Package Style:	20-pin DIP
Test Engineer:	A. Karygiannis

TABLE II. Radiation Schedule for 54AC521

EVENTS	DATE
1) Initial (Pre-Irradiation) Electrical Measurements	07/16/91
2) 10-KRAD IRRADIATION (0.5 krads/hour) POST-10-KRAD ELECTRICAL MEASUREMENT	11/18/91 11/19/91
3) 20-KRAD IRRADIATION (0.5 krads/hour) POST-20-KRAD ELECTRICAL MEASUREMENT	11/19/91 11/20/91
4) 30-KRAD IRRADIATION (0.5 krads/hour) POST-30-KRAD ELECTRICAL MEASUREMENT	11/20/91 11/21/91
5) 50-KRAD IRRADIATION (1.0 krads/hour) POST-50-KRAD ELECTRICAL MEASUREMENT	11/21/91 11/22/91
6) 75-KRAD IRRADIATION (1.4 krads/hour) POST-75-KRAD ELECTRICAL MEASUREMENT	11/22/91 11/23/91
7) 100-KRAD IRRADIATION (0.6 KRADS/HOUR) POST-100-KRAD ELECTRICAL MEASUREMENT	11/23/91 11/25/91
8) 24 HOURS ANNEALING AT +25°C POST-24-HOURS ELECTRICAL MEASUREMENT	11/25/91 11/26/91
9) 168 HOURS ANNEALING AT +25°C POST-168-HOURS ELECTRICAL MEASUREMENT	11/25/91 12/02/91
10) 200-KRAD IRRADIATION (5.2 KRADS/HOUR) POST-200-KRAD ELECTRICAL MEASUREMENTS	12/02/91 12/03/91
11) 300-KRAD IRRADIATION (5.0 KRADS/HOUR) POST-300-KRAD ELECTRICAL MEASUREMENTS	12/03/91 12/04/91
12) 168 HOURS ANNEALING AT +100°C POST-168 HOURS AT +100°C ELECTRICAL MEASUREMENTS	12/04/91 12/13/91

Notes:

- All parts were radiated under bias at the cobalt-60 gamma ray facility at GSFC.
- All electrical measurements were performed off-site at +25°C.
- All annealings were performed under bias.

Table III. Electrical Characteristics of 54AC521

FUNCTIONAL TESTS							
PARAMETER	VCC	VIL	VIH	CONDITIONS	PINS	LIMITS AT +25C/-55C,+125C	
FUNCT # 1	5.5V	0.00V	4.50V	FREQ = 1 MHz ALL I/O	VOL<1.5V / VDH>1.5V		
FUNCT # 2	5.5V	0.00V	2.50V	FREQ = 1 MHz ALL I/O	VOL<1.5V / VDH>1.5V		
DC PARAMETRIC TESTS							
PARAMETER	VCC	VIL	VIH	CONDITIONS	PINS	LIMITS AT +25C	
VGH1	3.0V	0.90V	2.10V	LOAD= -500A	DUTS	>+2.9V	, <+6.0V
VGH2	4.5V	1.35V	3.15V	LOAD= -500A	DUTS	>+4.4V	, <+6.0V
VGH3	5.5V	1.65V	3.65V	LOAD= -500A	DUTS	>+5.5V	, <+6.0V
VGH4	5.0V	0.90V	2.10V	LOAD= -12MA	DUTS	>+2.56V	, <+6.0V
VUHS	2.5V	1.35V	3.15V	LOAD= -24mA	DUTS	>+3.86V	, <+6.0V
VUH6	5.5V	1.65V	3.65V	LOAD= -24mA	DUTS	>+4.86V	, <+6.0V
PARAMETER	VCC	VIL	VIH	CONDITIONS	PINS	LIMITS AT +25C	
VOL1	3.0V	0.90V	2.10V	LOAD= +500A	DUTS	>+0.0V	, <+0.1V
VOL2	4.5V	1.35V	3.15V	LOAD= +500A	DUTS	>+0.0V	, <+0.1V
VOL3	5.5V	1.65V	3.65V	LOAD= +500A	DUTS	>+0.0V	, <+0.1V
VOL4	5.0V	0.90V	2.10V	LOAD= +12MA	DUTS	>+0.0V	, <+0.36V
VOL5	2.5V	1.35V	3.15V	LOAD= +24mA	DUTS	>+0.0V	, <+0.36V
VOL6	5.5V	1.65V	3.65V	LOAD= +24mA	DUTS	>+0.0V	, <+0.36V
PARAMETER	VCC	VIL	VIH	CONDITIONS	PINS	LIMITS AT +25C	
VISH	5.5V	1.65V	3.65V	LOAD= -500A	DUTS	>+3.85V	, <+6.0V
VISL	5.5V	1.65V	3.65V	LOAD= +500A	DUTS	>+0.0V	, <+1.65V
PARAMETER	VCC	VIL	VIH	CONDITIONS	PINS	LIMITS AT +25C	
IIH	5.5V	0.0V	5.5V	VIN = 5.5V	INS	>-0.0UA	, <+0.1UA
ILL	5.5V	0.0V	3.3V	VIN = 0.0V	INS	>-0.1UA	, <+0.0UA
PARAMETER	VCC	VIL	VIH	CONDITIONS	PINS	LIMITS AT +25C	
ICCH	5.5V	0.0V	5.5V	VTN = VCC	VCC	>+0.0UA	, <+8.0UA
ICCL	5.5V	0.0V	5.5V	VTN = 0.0V	VCC	>+0.0UA	, <+3.0UA
AC PARAMETRIC TESTS							
PARAMETER	VCC	VIL	VIH	CONDITIONS	PINS	LIMITS AT +25C	
TPLH1_A	3.0V	0.0V	3.0V	F=1MHz,VCMP=1.50V	OUTPUTS	> 1.0ns	, < 12.5ns
TPLH1_A	3.0V	0.0V	3.0V	F=1MHz,VCMP=1.50V	OUTPUTS	> 1.0ns	, < 12.5ns
TPLH1_B	3.0V	0.0V	3.0V	F=1MHz,VCMP=1.50V	OUTPUTS	> 1.0ns	, < 12.5ns
TPLH1_B	3.0V	0.0V	3.0V	F=1MHz,VCMP=1.50V	OUTPUTS	> 1.0ns	, < 12.5ns
TPLH1_I	3.0V	0.0V	3.0V	F=1MHz,VCMP=1.50V	OUTPUTS	> 1.0ns	, < 12.5ns
TPLH1_I	3.0V	0.0V	3.0V	F=1MHz,VCMP=1.50V	OUTPUTS	> 1.0ns	, < 9.0ns
PARAMETER	VCC	VIL	VIH	CONDITIONS	PINS	LIMITS AT +25C	
TPLH2_A	4.5V	0.0V	4.5V	F=1MHz,VCMP=2.25V	OUTPUTS	> 1.0ns	, < 9.0ns
TPLH2_A	4.5V	0.0V	4.5V	F=1MHz,VCMP=2.25V	OUTPUTS	> 1.0ns	, < 9.0ns
TPLH2_B	4.5V	0.0V	4.5V	F=1MHz,VCMP=2.25V	OUTPUTS	> 1.0ns	, < 9.0ns
TPLH2_B	4.5V	0.0V	4.5V	F=1MHz,VCMP=2.25V	OUTPUTS	> 1.0ns	, < 9.0ns
TPLH2_I	4.5V	0.0V	4.5V	F=1MHz,VCMP=2.25V	OUTPUTS	> 1.0ns	, < 9.0ns
TPLH2_I	4.5V	0.0V	4.5V	F=1MHz,VCMP=2.25V	OUTPUTS	> 1.0ns	, < 6.5ns
COMMENTS/EXCEPTIONS							
(1) VIL & VIH WERE TESTED DURING VOL & VDH TESTS AS GO/NOGO.							

TABLE IV: Summary of Electrical Measurements After
Total Dose Exposures and Annealing for 54AC521DMQB

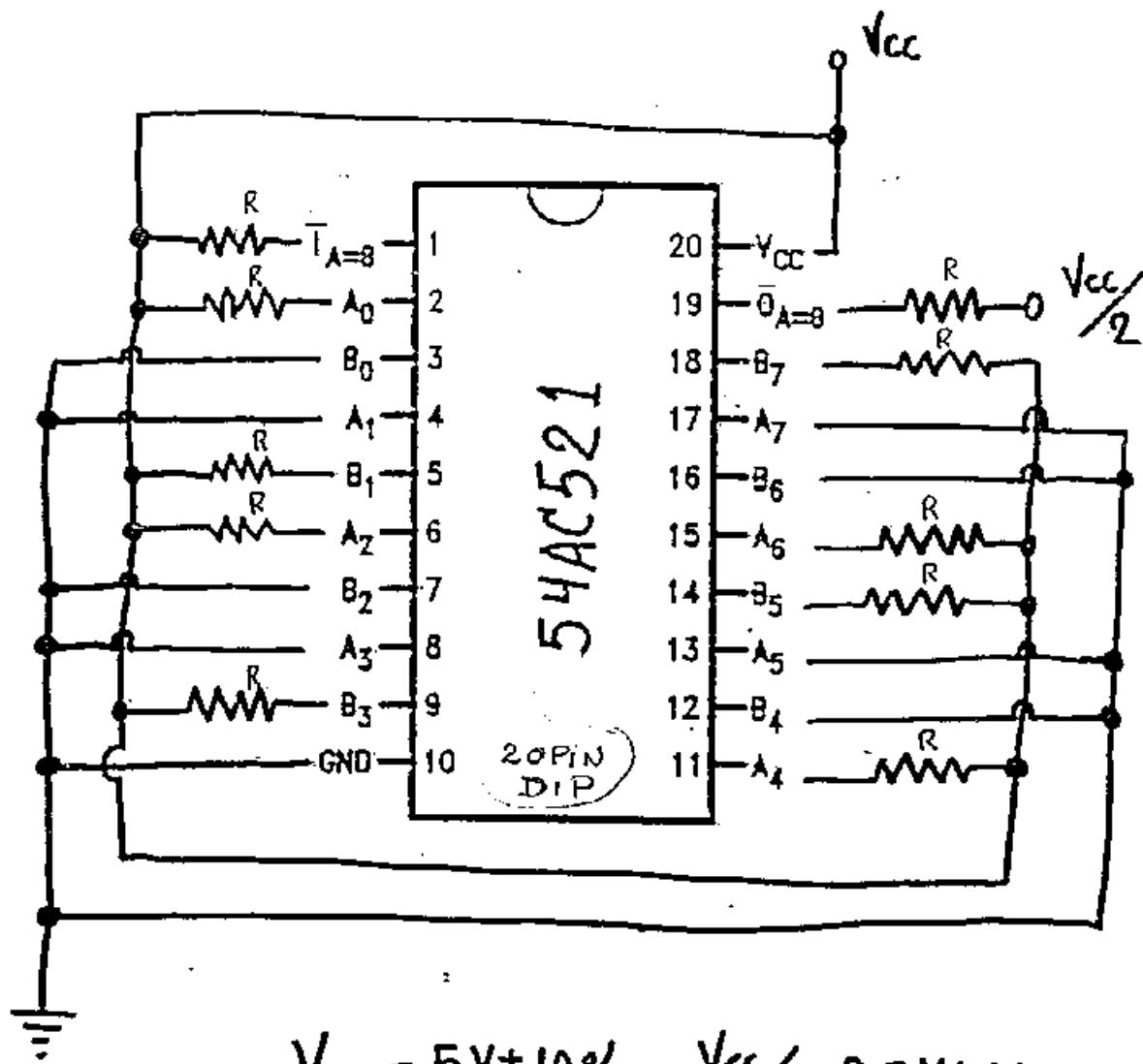
Parameter	Spec. Limits	Total Dose Exposure (TDE) (krads)												Anneal 168 hours +25°C	Total Dose (krads)			Anneal 168 hours +100°C		
		0 (Pre-Rad)		10		20		30		50		100			200		300			
		min	max	mean	sd		mean	sd	mean	sd										
FUNCI VCC = 4.5V		P		P		P		P		P		P		P		P		P		
FUNC2 VCC = 5.5V		P		P		P		P		P		P		P		P		P		
VOD1 V	2.9	6	2.99	0.00	2.99	0.00	2.99	0.00	2.99	0.00	2.99	0.00	2.99	0.00	2.99	0.00	2.99	0.00		
VOD2 V	4.4	6	4.49	0.00	4.49	0.00	4.49	0.00	4.49	0.00	4.49	0.00	4.49	0.02	4.43	0.00	4.49	0.00		
VOD3 V	5.4	6	5.49	0.00	5.49	0.00	5.49	0.00	5.49	0.00	5.49	0.00	5.47	0.04	5.48	0.00	5.49	0.00		
VOD4 V	2.56	6	2.79	0.01	2.79	0.01	2.79	0.01	2.79	0.00	2.79	0.01	2.79	0.05	2.77	0.01	2.75	0.01		
VOD5 V	3.86	6	4.20	0.01	4.20	0.01	4.20	0.01	4.20	0.01	4.19	0.01	4.18	0.05	4.16	0.01	4.17	0.01		
VOD6 V	4.86	6	5.24	0.01	5.24	0.01	5.24	0.01	5.24	0.01	5.23	0.01	5.22	0.05	5.22	0.01	5.21	0.01		
VODH V	3.85	6	4.95	0.02	4.95	0.02	4.95	0.02	4.95	0.02	4.94	0.02	4.92	0.05	4.91	0.02	4.89	0.04		
VOL1 V	0	0.1	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0		
VCL2 V	0	0.1	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0		
VOL3 V	0	0.1	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0		
VOL4 V	0	0.36	0.13	0.00	0.13	0.00	0.13	0.00	0.13	0.00	0.13	0.00	0.13	0.00	0.13	0.00	0.13	0.00		
VOLS V	0	0.36	0.18	0.00	0.19	0.00	0.19	0.01	0.18	0.00	0.18	0.00	0.19	0.00	0.19	0.00	0.20	0.01		
VOL6 V	0	0.36	0.16	0.00	0.16	0.00	0.17	0.01	0.16	0.00	0.16	0.00	0.16	0.00	0.17	0.00	0.16	0.02		
VIOL V	0	1.65	0.34	0.01	0.35	0.01	0.36	0.02	0.35	0.01	0.35	0.01	0.35	0.01	0.36	0.01	0.33	0.04		
IIR nA	0	100	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0		
IIL nA	-100	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0		
ICCH mA	0	0.008	0	0	0.12	0.1	1.2	0.9	3.0	1.6	5.1	3.0	19.1	5.5	10.6	5.1	21.9	7.3		
ICCL mA	0	0.008	0	0	0.04	0.0	0.6	0.5	2.0	1.4	4.3	2.7	17.1	5.5	10.7	5.2	22.8	7.9		
TPLH_A ns	1	12.5	6.9	0.3	7.7	0.4	6.9	0.4	7.7	0.4	7.6	0.5	7.6	0.4	7.1	0.36	6.9	0.3		
TPLH_A ns	1	12.5	8.0	0.4	9.7	0.4	9.0	0.4	9.6	0.4	9.7	0.4	9.6	0.5	9.9	0.5	9.9	0.5		
TPLH_B ns	1	12.5	6.6	0.3	7.4	0.3	6.6	0.3	7.4	0.4	7.4	0.4	7.4	0.4	7.5	0.3	7.4	0.5		
TPLH_B ns	1	12.5	8.0	0.4	9.1	0.5	8.4	0.4	9.0	0.5	9.0	0.5	9.0	0.5	9.0	0.49	8.6	0.5		
TPLH_I ns	1	9	5.4	0.3	6.0	0.3	5.3	0.3	6.0	0.3	5.9	0.3	5.8	0.2	5.4	0.25	5.1	0.2		
TPLH_I ns	1	9	5.4	0.3	6.7	0.3	6.0	0.3	6.8	0.3	6.9	0.3	6.9	0.3	6.9	0.28	7.1	0.3		

Notes:

1/ The mean and standard deviation values were calculated over the eight parts irradiated in this testing. The control samples remained constant throughout the testing and are not included in this table.

2/ Table IV provides radiation characteristics of parts at selected total dose exposures and annealing treatments. The data at other radiation exposures and annealing treatments is available and can be obtained upon request.

Figure 1. Radiation Bias Circuit for 54AC521



$$V_{CC} = 5V \pm 10\% , V_{CC}/2 = 2.5V \pm 10\%$$

$$R = 1K\Omega \text{HM} \pm 5\% , \frac{1}{4}W$$

$$T_A = +25^\circ C$$